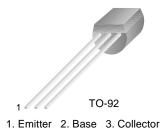


### SS9015

# Low Frequency, Low Noise Amplifier • Complement to SS9014



## **PNP Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	-50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-45	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-100	mA
P <sub>C</sub>	Collector Power Dissipation	450	mW
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

### **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = -100 \mu A, I_E = 0$	-50			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = -1 \text{mA}, I_B = 0$	-45			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -100 \mu A, I_C = 0$	-5			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = -50V, I_{E} = 0$			-50	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			-50	nA
h <sub>FE</sub>	DC Current Gain	$V_{CE} = -5V, I_{C} = -1mA$	60		1000	
V <sub>CE</sub> (sat)	Collector-Base Saturation Voltage	$I_C = -100 \text{mA}, I_B = -5 \text{mA}$			-0.7	
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = -100 \text{mA}, I_B = -5 \text{mA}$			-1.0	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE} = -5V, I_{C} = -2mA$	-0.6		-0.75	V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = -10V, I <sub>E</sub> =0 f=1MHz		4.5	7.0	pF
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = -5V, I_{C} = -10mA$	100	190		MHz
NF	Noise Figure	$V_{CE}$ = -5V, $I_{C}$ = -0.2mA f=1KHz, $R_{S}$ =1K $\Omega$		0.7	10	dB

## h<sub>FE</sub> Classification

Classification	A	В	С	D
h <sub>FE</sub>	60 ~ 150	100 ~ 300	200 ~ 600	400 ~ 1000

# **Typical Characteristics**

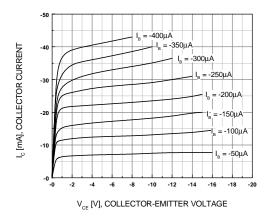


Figure 1. Static Characteristic

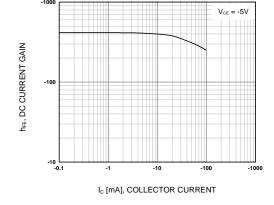


Figure 2. DC current Gain

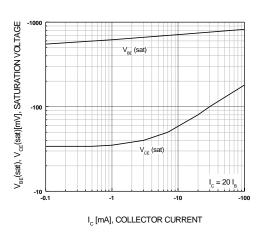


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

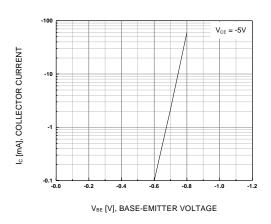


Figure 4. Base-Emitter On Voltage

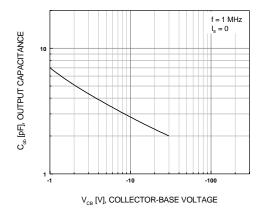


Figure 5. Collector Output Capacitance

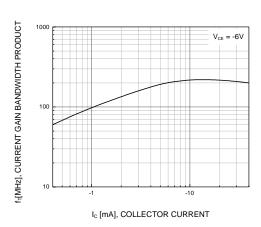
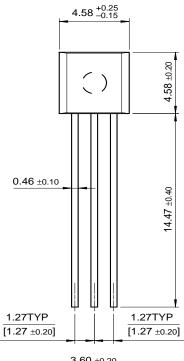


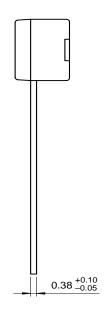
Figure 6. Current Gian Bandwidth Product

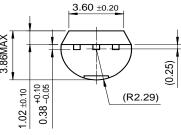
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# **Package Dimensions**

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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
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EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	I <sup>2</sup> C <sup>TM</sup>	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board.	. Around the world.™	OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	$VCX^{TM}$
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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